

WHAT IS CLAIMED IS:

1. A fabrication method of Ge-Mn magnetic semiconductor with a high Curie temperature, comprising the steps of:

designing a thin film of Ge-Mn alloy by reflecting the thermodynamic characteristics of Ge semiconductor and Mn magnetic metal; and

applying different heat energy to each of Ge semiconductor and Mn magnetic metal using the co-thermal evaporation method and fabricating a thin film of amorphous Ge-Mn alloy using the co-thermal evaporation method.

2. The method as claimed in Claim 1, wherein said thin film of Ge-Mn alloy maintains a single phase and the microstructure of the alloy is an amorphous structure in order to contain a high percentage (0 - 48 atomic %) of magnetic metal.